

**AMENDMENTS TO THE SPECIFICATION**

**Please replace the first full paragraph on page 6 with the following rewritten paragraph:**

**Brief Description of the Drawing**

Figs. 1(A) and 1(B) are views ~~Fig. 1 is a view~~ showing a schematic constitution of a CCD imaging device to be used in an embodiment of the invention, with (A) being a plane, and (B) being a cross-sectional view taken on line IB-IB;

Fig. 2 is a cross-sectional view taken on line IB-IB showing a schematic constitution of a CCD imaging device to be used in an embodiment of the invention;

Fig. 3 is a plane view showing the constitution of the solid state imaging device in accordance with the embodiment of the invention; and

Figs. 4(A) and 4(B) are views ~~Fig. 4 is a view~~ showing the constitution of a contact hole portion in the embodiment, with (A) being a plane, and (B) being a cross-sectional view taken on line IVB-IVB.

101 denotes a first layer (polysilicon electrode), 102 denotes a second layer (polysilicon electrode), 105 denotes a light-receiving portion, 106 denotes a charge transfer channel, 107 denotes a read-out gate, 108 denotes an element-separating region (channel stop), 109 denotes an insulating membrane, each of 111, 112, 113 and 114 denotes a transfer electrode (polysilicon electrode), 122 denotes a vertical charge transfer portion (VCCD), 123 denotes a horizontal charge transfer portion (HCCD), 124 denotes a signal-reading circuit, 125 denotes a metal wiring, 126 denotes a contact hole, 127 denotes a polysilicon electrode, 129 denotes an insulating membrane and 130 denotes a wiring pattern.